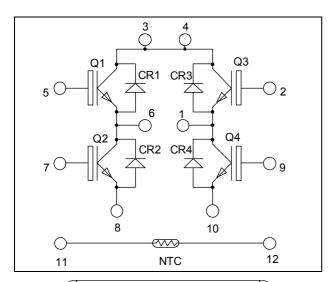
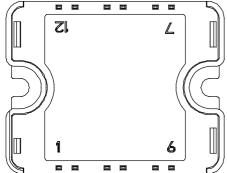


Full - Bridge NPT IGBT Power Module

$$V_{CES} = 1200V$$

 $I_C = 15A$ @ $Tc = 80$ °C





Pins 3/4 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) Fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	25	
I_{C}	Continuous Conector Current	$T_C = 80$ °C	15	Α
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	60	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25^{\circ}C$	140	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	30A@1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
T	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_j = 25^{\circ}C$			250	^
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE} = 1200V$	$T_j = 125$ °C			500	μΑ
17	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$	2.5	3.2	3.7	V
V _{CE(sat)}	Conector Enlitter Saturation Voltage	$I_C = 15A$	$T_j = 125$ °C		4.0		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1 \text{mA}$		4		6	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V$, $V_{CE} = 0V$				400	nA

Dynamic Characteristics

•	Characteristic	Test Conditions		Min	Тур	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			1000		pF
Coes	Output Capacitance				150		
C_{res}	Reverse Transfer Capacitance	f = 1MHz			70		
Q_g	Total gate Charge	$V_{GE} = 15V$			99		
Q_{ge}	Gate – Emitter Charge	$V_{Bus} = 600V$			10		nC
Q_{gc}	Gate – Collector Charge	$I_C=15A$			70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	ning (25°C)		60		
T_{r}	Rise Time	$V_{GE} = 15V$			50		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 600V$ $I_{\text{C}} = 15A$			315		ns
T_{f}	Fall Time	$R_G = 33\Omega$			30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = 15V$			60		
T_{r}	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 15A$			356		ns
$T_{\rm f}$	Fall Time	$R_G = 33\Omega$			40		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 600V$	$T_j = 125$ °C		2		
E_{off}	Turn-off Switching Energy	$I_C = 15A$ $R_G = 33\Omega$	$T_j = 125$ °C		1		mJ

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Test Conditions		Тур	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Payarga Laglaga Current	$V_R=1200V$ T_j	$T_j = 25$ °C			100	Δ
1 _{RM}	Maximum Reverse Leakage Current	V _R -1200 V	$T_j = 125$ °C			500	μA
I_F	DC Forward Current		$Tc = 80^{\circ}C$		15		A
	Diode Forward Voltage	$I_F = 15A$			2.8	3.3	
$V_{\rm F}$		$I_F = 30A$			3.4		V
		$I_F = 15A$	$T_j = 125$ °C		2.4		
t _{rr}	Reverse Recovery Time	$I_F = 15A$ $V_R = 800V$	$T_j = 25^{\circ}C$		240		ns
ι _{rr}	Reverse Recovery Time		$T_{j} = 125^{\circ}C$		290		113
Q _{rr}	Reverse Recovery Charge	$di/dt = 200 A/\mu s$	$T_j = 25$ °C		260		nC
			$T_{j} = 125^{\circ}C$		960		iiC



Thermal and package characteristics

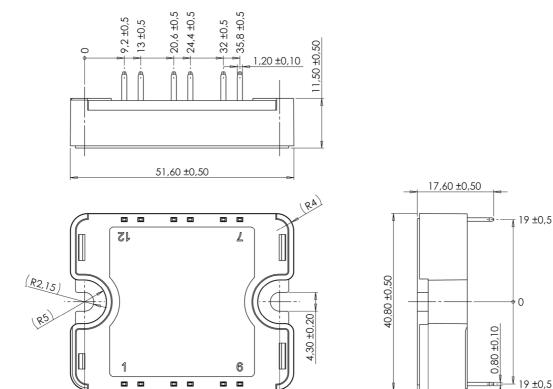
Symbol	Characteristic			Min	Typ	Max	Unit
D	Junction to Case Thermal Resistance	IGBT			0.9	°C/W	
R_{thJC}	Junction to Case Thermal Resistance		Diode			2	C/ W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		150	
T_{STG}	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature					100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight				80	g	

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature R_T: Thermistor value at T

SP1 Package outline (dimensions in mm)



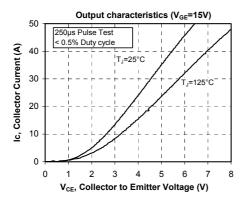
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

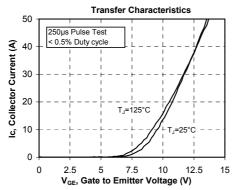
2,50 ±0,20

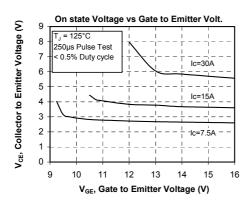
45 ±0,20

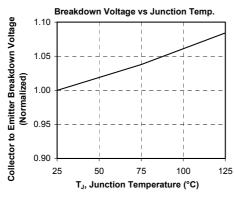


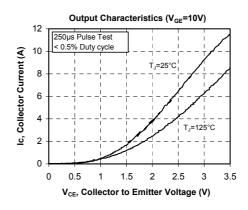
Typical Performance Curve

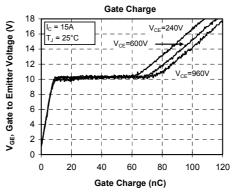


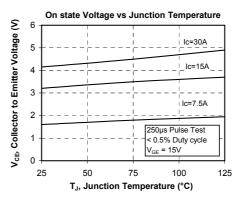


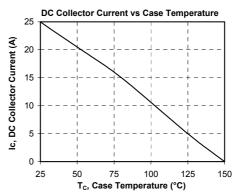




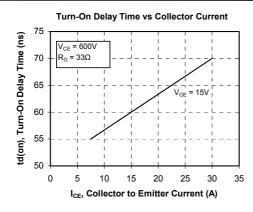


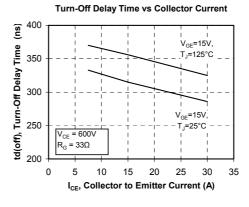


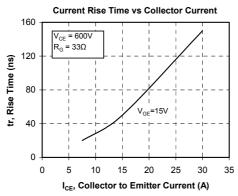


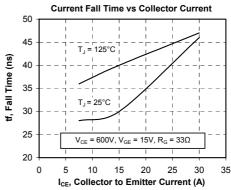


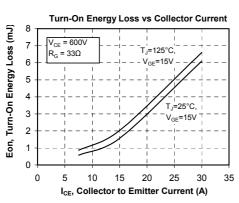


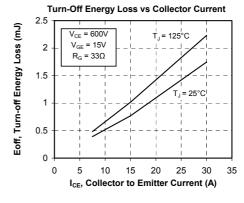


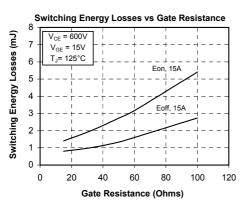


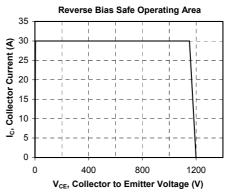




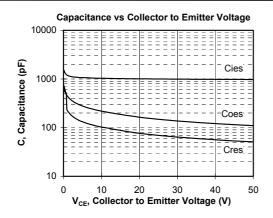


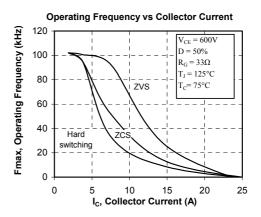


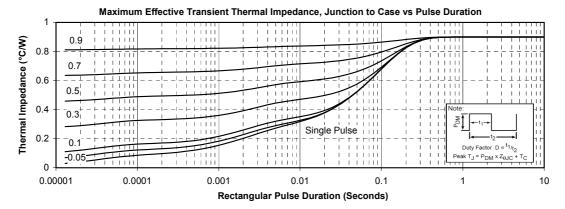












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